

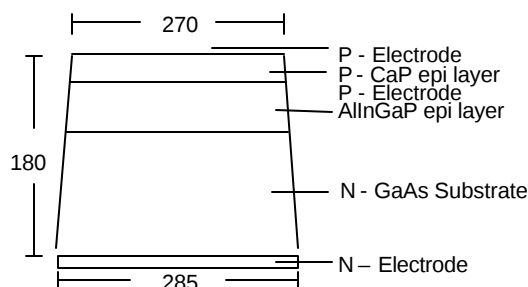
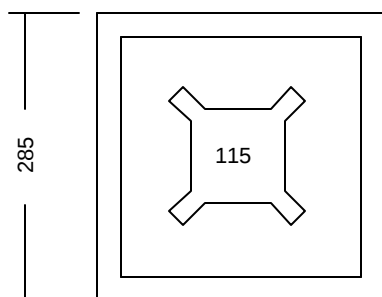
TCO12UGU



- ❖ Features:
 - AlInGaP/GaAs Ultra Bright LED Chips
 - MOVPE Process Wafer
 - Suitable for new creative products

- ❖ Typical Applications
 - SMD LED Chip
 - Backlight
 - Message Boards
 - Commercial Applications

- ❖ Outline Dimensions:



- ❖ Physical Structure:

Physical Structure:				
Chip dimensions		Chip size	11 mil x 11 mil	285 μm x 285 μm
		Thickness	7 mil	180 μm
		Emission area	11 mil	270 μm
		Bonding pad	4.5 mil	115 μm
Electrode	Top	P (anode)	Gold (Aluminium optional)	
	Backside	N (cathode)	Gold alloy	
Surface condition		Not frosted		

- ❖ Electro-Optical Characteristics:

Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Forward Voltage	V_F	$I_F = 20\text{mA}$		2.00	2.40	V
Wavelength	λ_P	$I_F = 20\text{mA}$	-	564	-	nm
	Hue	$I_F = 20\text{mA}$	558	562	566	
Spectral width at half height	$\Delta\lambda$	$I_F = 20\text{mA}$	-	20	-	nm
Reverse Voltage	V_R	$I_R = 10\mu\text{A}$	5	-	-	V
Luminous Intensity	I_v	$I_F = 20\text{mA}$	10	-	-	mcd
			15	-	-	

- ❖ Note. Also available:

Chip size		Luminous intensity
mils	μ m	mcd
9	210 x 210	5
9	210 x 210	10

GREEN